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EDUCATION

1958 BSc. Engineering Physics, Queen's University
1959 MSc. Nuclear Physics, University of British Columbia
1963 Ph.D. Theoretical Particle Physics, Princeton University

PROFESSIONAL EXPERIENCE (36 years of service to UMaine)

2006-Present Emeritus Professor
1986-1987 Oregon Graduate Center
1980-1986 Chairman
1978-2006 Professor
1970-1978 Associate Professor
1977 Summer Visitor at Brookhaven National Laboratory
(5 weeks)
1970 Summer Visitor at Argonne National Laboratory
(3 weeks)
1964-1970 Assistant Professor, Dartmouth College
1963-1964 Princeton University, Instructor
1960-1963 Princeton University, Teaching Assistant
1959-1960 Princeton University, Research Assistant

PROFESSIONAL SOCIETIES

American Physical Society, American Association of Physics Teachers

PRINCIPAL PUBLICATIONS (1993-2007)

"Silicon donor-hydrogen complex in GaAs: a deep donor?", R.A. Morrow, J. Appl. Phys., **74**, 6164 (1993)

"Participation of EL2 in the donor activation of silicon implanted into GaAs" (with P. Kengkan and A. Mealing), Physical Review B **49**, 16309 (1994).

"High-temperature annealing of semi-insulating GaAs and the dissociation of EL2", J. Appl. Phys. **78** 5116 (1995)

"Theory of EL2 and EL5 formation in melt-grown GaAs", J. Appl. Phys. **77** 3843 (1995).

"Diffusing arsenic vacancies and their interaction with the native defect EL2 in GaAs., (with K.M. Luken), J. Appl. Phys. **79**, 1988 (1996).

"Formation energies and charge states of native defects in GaAs: A selected compilation from the literature", (with K.M. Luken) Semiconductor Science and Technology **11**, 1156 (1996).

Richard A. Morrow (continued)

PRINCIPAL PUBLICATIONS (cont.)

“Model of Defect Reactions in Melt-Grown GaAs”, Defect and Diffusion Forum 138-139, **35** (1996).

“Defect Formation in GaAs grown by organometallic vapor phase epitaxy and the structure of EL2”, J.Crystal Growth 241, 57 (2002).

“Kinetics of dopant incorporation in GaAs grown by organometallic vapor phase epitaxy”, J.Crystal Growth 300, 284 (2007).